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APPLICATION AS PUBLISHED OR REPUBLISHED**

Date of mailing (*day/month/year*)
07 October 2004 (07.10.2004)

Applicant's or agent's file reference
CFO17975WO

IMPORTANT NOTICE

International application No.
PCT/JP2004/004072

International filing date (day/month/year)
24 March 2004 (24.03.2004)

Priority date (*day/month/year*)
26 March 2003 (26.03.2003)

Applicant

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The International Bureau transmits herewith the following documents:

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Facsimile No.+41 22 338 70 10

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
7 October 2004 (07.10.2004)

PCT

(10) International Publication Number
WO 2004/086516 A1

(51) International Patent Classification⁷: H01L 31/06

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(21) International Application Number:

PCT/JP2004/004072

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(22) International Filing Date: 24 March 2004 (24.03.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-084537 26 March 2003 (26.03.2003) JP

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

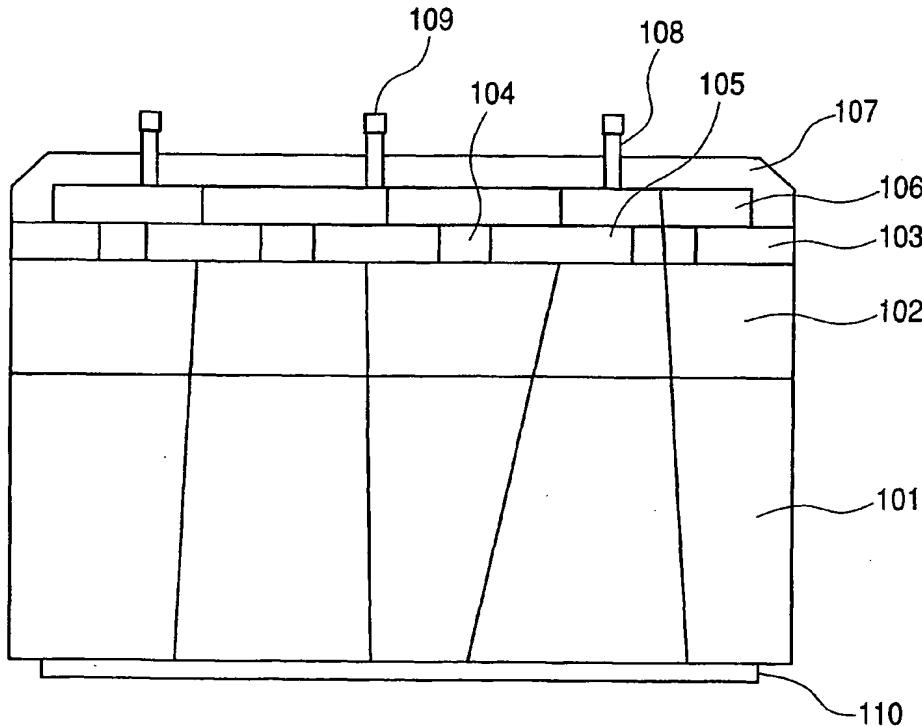
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(54) Title: SOLAR CELL



(57) Abstract: Provided is a solar cell having a silicon substrate for a solar cell, the substrate being formed by allowing a high-purity polycrystalline silicon layer to grow on a surface of a base that is sliced from a polycrystalline silicon ingot which is obtained by melting metal-grade silicon and solidifying the silicon in one direction, wherein a layer having a non-doped amorphous silicon phase and a microcrystalline silicon phase mixed together is stacked on the high-purity polycrystalline silicon layer.

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